LH0086/LH0086C Digitally-Programmable-Gain Amplifier

General Description

The LH0086 is a self-contained, high-accuracy, digitally-programmable-gain amplifier. It consists of a FET-input operational amplifier, a precision resistor ladder, and a digitallyprogrammable switch network. A three-bit TTL-compatible digital input selects accurate gain settings of 1, 2, 5, 10, 20, 50, 100, or 200.

The LH0086 exhibits low offset voltage, high input impedance, fast settling, high power supply rejection ratio, and excellent gain accuracy and gain non-linearity.

The LH0086 is specified for operation from -55° C to $+125^{\circ}$ C. The LH0086C is specified from -25° C to $+85^{\circ}$ C. Both devices are hermetically sealed in a 14-lead dual-inline metal package.

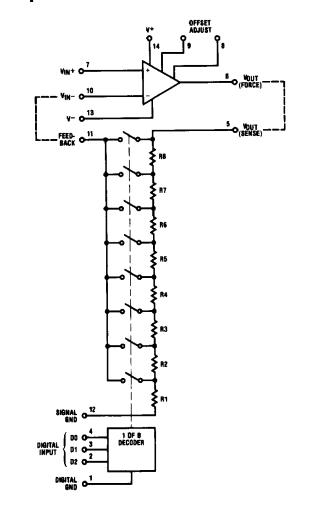
Features

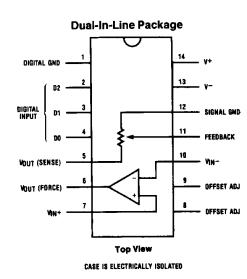
- 0.01% maximum gain accuracy at gain=1
- 0.005% typical gain non-linearity
- 1 ppm/°C typical gain drift
- $10^{10}\Omega$ input impedance
- 80 dB minimum PSRR.
- TTL-compatible digital inputs
- 2 μs settling to 0.01%

Applications

- Data acquisition systems
- Auto range DVMs
- Adaptive servo loops

Simplified Schematic and Connection Diagrams





Order Number LH0086D or LH0086CD See NS Package Number D14F

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Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications. (Note 5)

٧s	Supply Voltage (Note 1)	± 18V
VIN	Analog Input Voltage (Note 2)	±15V
V _{IL(H)}	Digital Input Voltage	$-4V_{,}+V_{S}$
PD	Power Dissipation	500 mW
	Output Short Circuit Duration	Continuous

T _A Operating Temperature Range:	
LH0086	55°C to + 125°C
LH0086C	-25°C to +85°C
T _{STG} Storage Temperature	-65°C to +150°C
Lead Temperature	
(Soldering, 10 seconds)	+ 300°C
ESD rating to be determined.	

DC Electrical Characteristics

 $V_S = \pm 15V$, $R_L = 10 \text{ k}\Omega$, $T_{MIN} \le T_A \le T_{MAX}$, Pin 10 connected to Pin 11, Pin 5 connected to Pin 6 (Non-inverting)

Symbol	Parameter	Conditions		LH0086				LH00860	;	
				Min	Тур	Max	Min	Min Typ Max	Max	Units
V _{OS}	Input Offset Voltage		T _J =25°C		0.3	5.0		0.3	10	
						7.0			13	mV
V _{OS} /ΔT	Input Offset Voltage Change with Temperature	V _{IN} =0V			10			10		μ٧/°(
I _B	Input Bias Current	(Notes 3, 4)	T _J =25°C		100	500		100	500	pА
						500			100	nA
R _{IN}	Input Resistance				10			10		GΩ
VIN	Input Voltage Range			±10	±11.5		±10	±11.5		v
Av	Voltage Gain				1.0			1.0		
					2.0			2.0		
		See Table 1			5.0			5.0		
		for Digital Gain-			10			10		v/v
		Control Codes			20			20		
					50			50		
i					100			100		
					200			200		
	Gain Error	$A_V = 1$ $A_V = 2,5$ $A_V = 10,20$ $A_V = 50,100,200$	T _A =25°C		0.003 0.03 0.05 0.1	0.01 0.05 0.1 0.3		0.003 0.05 0.1 0.15	0.03 0.1 0.2 0.4	%
		$A_V = 1$ $A_V = 2,5$ $A_V = 10,20$ $A_V = 50,100,200$			0.003 0.03 0.1 0.15	0.02 0.1 0.2 0.4		0.003 0.05 0.1 0.15	0.06 0.2 0.3 0.5	70
	Gain Non-Linearity	A _V =1	T _A =25°C		0.002			0.002		0/
					0.005			0.005		%
$\Delta A_V / \Delta T$	Gain Temperature Coefficient	A _V =1			1.0			1.0		ppm/°
PSRR	Power Supply Rejection Ratio	$\pm 8V \le V_S \le \pm 18V$		80	90		70	90		dB
vo	Output Voltage Swing	$R_L \ge 10 k\Omega$		±10	±12	_	±10	±12		v

Note 1: Improper supply power-on sequence may damage the device. See Power Supply Connection Section under Applications Information.

Note 2: for supply voltages less than $\pm 15V$ the maximum input voltage is equal to the supply voltage.

Note 3: Due to short production test time, these parameters are specified at junction temperature, $T_J \approx 25^{\circ}$ C. In normal operation the junction temperature rises above the ambient temperature, T_A , as a result of the internal power dissipation, PD. $T_J \approx T_A + \theta_{JA} \times PD$ where θ_{JA} is the thermal resistance from junction to ambient (typically 65°C/W).

Note 4: The input bias currents are junction leakage currents which approximately double for every 10°C increase in junction temperature.

Note 5: Refer to RETS0086D for LH0086D military specifications.

LH0086/LH0086C

DC Electrical Characteristics (Continued)

 $V_S = \pm 15V$, $R_L = 10 \text{ k}\Omega$, $T_{MIN} \le T_A \le T_{MAX}$, Pin 10 connected to Pin 11, Pin 5 connected to Pin 6 (Non-inverting).

Symbol	Parameter	Conditions		LH0086			LH0086C			Units
Symbol				Min Typ	Тур	Max	Min	Тур	Max	
Isc	Output Short-Circuit Current		T _A =25°C	±5	±18	± 40	±5	±18	±40	mA
				±2		±40	±2		± 40	11/2
Ro	Output Resistance	A _{VCL} =1			0.05			0.05		Ω
VIL	Digital "0" Input Voltage					0.7			0.7	v
VIH	Digital "1" Input Voltage			2.0			2.0			
կլ	Digital "0" Input Current	V _{IN} =0.4V			1.5	4.0		1.5	4.0	μΑ
liH	Digital "1" Input Current	V _{IN} =2.4V			0.01			0.01		
Vs	Supply Voltage Range			±8.0		±18	±8.0		±18	V
Is ⁽⁺⁾	Positive Supply Current	$V_{S} = \pm 18V$			8.5	15.5		8.5	15.5	mA
I _S (-)	Negative Supply Current				-4.5	-8.5		-4.5	-8.5	

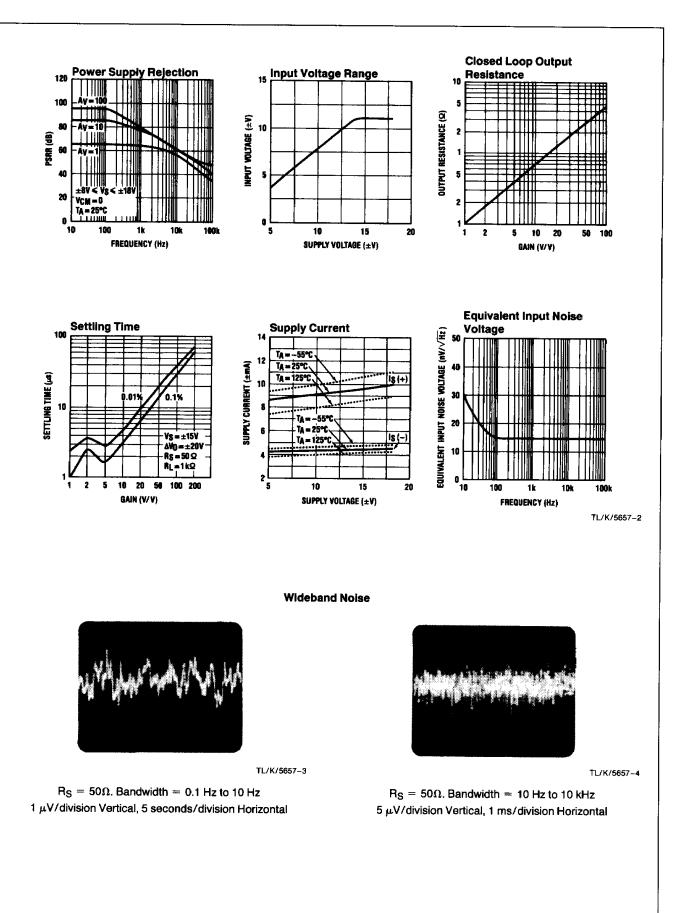
AC Electrical Characteristics

 $V_S = \pm 15V$, $T_A = 25^{\circ}$ C, $R_L = 10 \text{ k}\Omega$, Pin 10 connected to Pin 11, Pin 5 connected to Pin 6 (Non-Inverting)

Symbol	Parameter	Co	nditions	Min	Тур	Max	Units
BW	Small Signal Bandwidth		A _V =1		3000		_
		—3 dB	A _V =50		60		
			A _V =200		15		kHz
			A _V =1		425		1112
		-1%	A _V = 50		8.5		
		1	A _V =200		2		
PBW	Power Bandwidth	V _O = ±10V			159		kHz
SR	Slew Rate	¥0- ⊥10¥			10		V/µs
			A _V =1		2.5		
ts	Settling Time (<i>Figure 7</i>) 0.01%	$\Delta V_{O} = 20V$	A _V =50		20		μs
			A _V =200		75		μs
ts	Settling Time After Gain Change				10		
θ _N	Equivalent Input Noise	R _S =100Ω	BW=0.1-10 Hz		3		μ∨р-р
	Voltage (Figure 6)	$A_V = 10002$	f=1 kHz		25		nV/1∕Hz
ĪN	Equivalent Input Noise Current				0.01		pA/√Hz

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Applications Information

Theory of Operation

The LH0086 is a digitally programmable gain amplifier with 3-bit digital gain control. It contains a FET-input operational amplifier, a precision resistor ladder, and a digitally programmable switch network.

The LH0086 was designed for use in a non-inverting configuration, thus the following discussion covers the LH0086 as used as a non-inverting amplifier. The gain of the LH0086 is given by the familiar gain equation of a non-inverting amplifier.

$$A_V = 1 + \frac{R_F}{R_S}$$

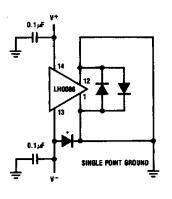
Each gain step is set by the ratio of the ladder resistors. The resistor ladder is constructed with high stability, low temperature-coefficient resistors precision laser-trimmed to the required values. FET switches are used to select the desired ratio. Since the FET switches are in series with the operational amplifier input, their "on resistance" and temperature drift do not degrade amplifier accuracy. The FET switches are selected by a 1 of 8 decoder, by applying the proper logic levels at digital inputs D0, D1, and D2. The gains are set as given in Table I.

TABLE I. Gain-Control Codes

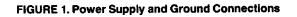
Gain	D2	D1	D0
1	0	0	0
2	0	0	1
5	0	1	0
10	0	1	1
20	1	0	0
50	1	0	1
100	1	1	0
200	1	1	1

Power Supply Connection

Proper power supply connections are shown in *Figure 1*. The power supplies should be bypassed to ground as close as possible to device supply pins. For most applications, the bypass capacitor should be 0.1 μ F.



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Care must be taken in the power-on sequence. The LH0086 may suffer irreversible damage if the V⁺ supply is applied prior to the powering on of the V⁻ supply. In most applications using dual-tracking supplies and with the device supply pins adequately bypassed, this will not present a problem. If this cannot be guaranteed, a germanium or Schottky protection diode should be connected between the digital ground pin and the V⁻ pin as shown in *Figure 1*.

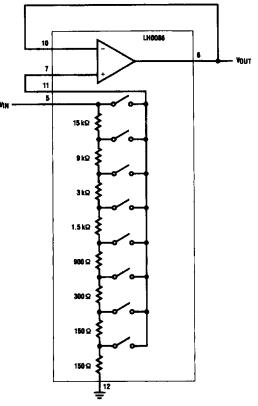
Grounding Considerations

Care should be taken in the connection of digital and analog grounds. Digital switching currents can introduce noise on the analog ground pin. If possible, both grounds should go to a ground plane beneath the device, otherwise each ground should be run separately to a single point ground. The idea is to keep digital current from passing through the analog ground line. If long ground leads are used, diode clamps should be placed as close to the device as possible (*Figure 1*).

Programmable Attenuator

The LH0086 may be used as a programmable attenuator when connected as in *Figure 2*. The accuracy of this attenuator will be typically 0.1%.

Note: Max. $V_{IN} = \pm 11$ Volts.



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LH0086/LH0086C

Applications Information (Continued)

TABLE II. Attenuator Codes

D2	D1	D0	Attenuation
0	0	0	1
0	0	1	2
0	1	0	5
0	1	1	10
1	0	0	20
1	0	1	50
1	1	0	100
1	1	1	200

Inverting Mode

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11

3

DQ

D1

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The LH0086 may be used in the inverting mode, however, there are several design considerations.

- 1. Input resistance is low at high gains (see gain chart for input resistance at each gain).
- 2. Each gain step gets a one subtracted from the non-inverting gain. (See inverting gain chart for available gains.)
- 3. The first gain step (digital code of 000) cannot be used because the output will remain at virtual ground regardless of the input.

LH0086

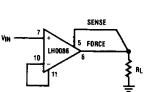
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TABLE III. Inverting Gain Chart

	D2	D1	DO	Gain	R_{IN} (Ω)
	0	0	0	A _V =0	30k
	0	0	1	$A_V = 1$	15k
	0	1	0	$A_V = 4$	6k
	0	1	1	$A_V = 9$	Зk
	1	0	0	$A_V = 19$	1.5k
ĺ	1	0	1	$A_V = 49$	600
	1	1	0	A _V = 99	300
	1	1	1	$A_{V} = 199$	150

Remote Output Sense

The VOUT sense pin of the LH0086 should be connected at the load in order to eliminate errors due to lead resistance. In any case the output sense and output force must be tied together at some point. See Figure 4.



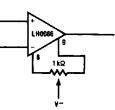


FIGURE 4. Remote Output Sense FIGURE 5. Offset Adjustment



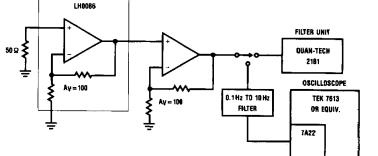
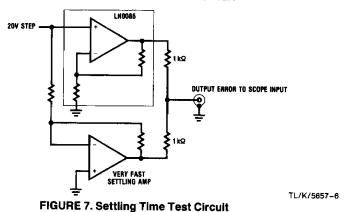


FIGURE 6. Noise Measurement Circuit



VOUT

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Definition of Terms

- Vos Offset Voltage: The voltage that must be applied to force the output to 0 volts.
- IB input Bias Current: The current into Pin 7 with the device connected in the non-inverting configuration.
- R_{IN} Input Resistance: The ratio of the change in input voltage to the change in input current on either input with the other grounded.
- V_{IN} Input Voltage Range: The voltage range for which the device is operational.
- **PSRR Power Supply Rejection Ratio:** The ratio of the specified change in supply voltage to the change in input offset voltage over this range.
- Av Voltage Gain: The ratio of output voltage change to the input voltage change producing it.

Gain Error: The deviation in percent between the ideal voltage gain and the value obtained when the device is configured for that gain.

Gain Non-Linearity: The deviation of the gain from a straight line drawn through the end-points expressed as a percent of full scale (10V for operation with \pm 15V supplies). For testing purposes it is the difference between positive swing gain (0V to 10V) and average gain (-10V to 10V) or between negative swing gain (0V to -10V) and average gain.

- Vo Output Voltage Swing: The peak output voltage swing referenced to ground into specified load.
- Io(sc) Output Short-Circuit Current: The current supplied by the device with the output connected directly to ground.
- **R**_O **Closed Loop Output Resistance:** The ratio of change in output voltage to change to output current at a specific gain.
- V_S Supply Voltage Range: The supply voltage range for which the device is operational.
- Is Supply Current: The current required from the supply to operate the device with no load and with the analog as well as the digital inputs at 0V.

- PD Power Dissipation: The power dissipated in the device with no load and with the analog as well as the digital inputs at 0V.
- V_{IH} Digital "1" Input Voltage: Minimum voltage required at the digital input to guarantee a high logic state.
- VIL Digital "0" Input Voltage: The current into a digital input at specified logic level.
- △V_{OS}/△T Average input Offset Voltage Drift: The ratio of input offset voltage change from 25°C to either temperature extreme divided by the temperature range.
- $\Delta A_V / \Delta T$ Average Gain Temperature Coefficient: The ratio in gain from 25°C to either temperature extreme divided by the temperature range.
- BW Bandwidth: The frequency at which the voltage gain is reduced to 3 dB below the low frequency value.
- **PBW Power Bandwidth:** Maximum frequency for which the output swing is a large signal sine-wave without noticeable distortion.
- SR Slew Rate: The internally limited rate of change in output voltage with a large amplitude step function applied at the input.
- ts Settling Time: The time between the initiation of an input step function and the time when the output voltage has settled to within a specified error band of the final output voltage.

Gain Switching Time: The time between the initiation of a gain logic change and the time when the final gain switches are closed. It includes overdrive recovery time, but not settling to final value.

- e_N Equivalent Input Noise Voltage: The rms or peak noise voltage referred to the input (RTI) over a specified frequency band.
- iN Equivalent Input Noise Current: The rms or peak noise current referred to the input (RTI) over a specified frequency band.

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